

**Features**

- **Fast Read Access Time - 55 ns**
- **Automatic Page Write Operation**  
Internal Address and Data Latches for 32 Bytes  
Internal Control Timer
- **Fast Write Cycle Times**  
Maximum Page Write Cycle Time: 2 ms  
1 to 32 Byte Page Write Operation
- **Low Power Dissipation**  
80 mA Active Current  
100  $\mu$ A CMOS Standby Current (28HC64L)
- **Direct Microprocessor Control**  
DATA Polling
- **High Reliability CMOS Technology**  
Endurance:  $10^4$  or  $10^5$  Cycles  
Data Retention: 10 years
- **Single 5 V  $\pm$  10% Supply**
- **CMOS and TTL Compatible Inputs and Outputs**
- **JEDEC Approved Byte-Wide Pinout**
- **Full Military, Commercial, and Industrial Temperature Ranges**

**64K (8K x 8)  
High Speed  
CMOS  
E<sup>2</sup>PROM**

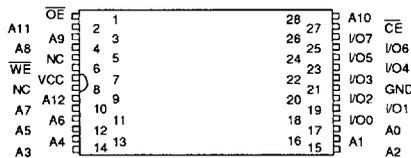
**Description**

The AT28HC64/L is a high-speed, low-power Electrically Erasable and Programmable Read Only Memory. Its 64K of memory is organized as 8,192 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 55 ns with power dissipation of just 440mW. When the device is deselected the standby current is less than 100  $\mu$ A.

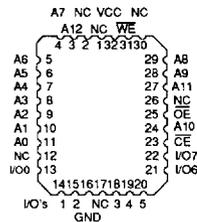
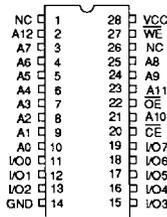
The AT28HC64/L is accessed like a Static RAM for the read or write cycles without the need for external components. The device contains a 32-byte page register to allow writing of up to 32 bytes simultaneously. During a write cycle, the addresses and 1 to 32 bytes of data are *(continued on next page)*

**Pin Configurations**

TSOP Top View



Pin Name	Function
A0 - A12	Addresses
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect



Note: PLCC package pins 1 and 17 are DON'T CONNECT.



